



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: **Jeon, et al.**

Serial No.: 10/618,273

Filed: July 11, 2003

For: **Method for Forming a Field Effect Transistor Having a High-K Gate Dielectric and Related Structure**

Art Unit: 2826

Examiner: Tran, Tan N.

AMENDMENT AND RESPONSE TO OFFICE ACTION

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir/Madam:

This is in response to the Office Action dated February 17, 2004 in the above-referenced patent application. Please enter and consider the following amendments and remarks.